

Edge State Transport in Separately Contacted Double-Layer Quantum Hall Systems

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We develop a theory of edge state transport in separately contacted double-layer quantum Hall systems which are tuned close to the resonance condition for tunneling between the layers. When applied to the case where contact is made to only one layer, the theory gives a quantized Hall resistance and zero longitudinal resistance in both weak and strong inter-layer coupling limits. For weak coupling, the leading correction to the Hall resistance occurs at second order, while the longitudinal resistance appears at first order. Recent experiments which show almost quantized Hall resistance and a substantial longitudinal resistance are explained and predictions are made for other contact configurations.

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Recently it has become possible to fabricate double-layer two-dimensional electron systems (2DES's) in which the two layers can be contacted separately [1–3]. This technological achievement has led to the development of several new experimental techniques for probing properties of two-dimensional electronic systems [3–6]. In one recent experiment Ohno and Sakaki [3] studied transport in the quantum Hall regime for a system in which contact was made to one layer while the other layer was left floating. When the system was tuned to equal layer densities to maximize coupling due to tunneling, they found that the transport coefficients were usually nearly identical to those measured when both layers were contacted. However, near quantum Hall plateaus the Hall resistivity nearly doubled in the floating layer case, and the longitudinal resistance rose to a finite value indicating the presence of dissipation inside the sample. These authors also observed local maxima in R_{xx} which bracket the local minima at the center of the quantum Hall plateaus. In this Rapid Communication we report on a theoretical study of transport in coupled, separately contacted, double-layer systems which was motivated by these experiments. We use our theoretical approach to predict behavior for contact geometries not yet realized experimentally.

We consider a double-layer 2DES on a quantum Hall plateau and assume that the transport currents are small enough so that the edge state picture of the quantum Hall effect is applicable [7]. For simplicity we assume that a single Landau level is occupied in each layer and that $k_B T$ is small compared to the Landau level separation $\hbar\omega_c$; the generalization of our theory to larger filling factors

is obvious. For a single-layer system the quantum Hall effect can be understood as a consequence of the spatial separation between left-going and right-going states on opposite edges of the sample which permits them to maintain a local equilibrium even when their chemical potentials differ and a net current is carried through the sample. In our model of edge state transport in double-layer systems with the Hall bar geometry illustrated in Fig. 1, we assume that equilibration between left-going states and right-going states is still negligible, but allow equilibration to occur between the two layers along both edges. In the experiments we have in mind, coupling between the two-layers occurs because of tunneling and we could calculate transport coefficients for a given contact configuration by using a multi-probe Landauer-Buttiker formula [8] and modeling inter probe transmission coefficients in a way which reflects the absence of back scattering within an electron layer. Instead we adopt a slightly different approach which reflects our belief that phase coherence inside the sample does not play any essential role in the physics we address. We emphasize, however, that our discussion could as easily be presented using the lexicon of Landauer-Buttiker transport theory, which provides an economical description of edge state transport in the quantum Hall regime [9].

On a quantum Hall plateau, the transport current can be calculated from the distribution function for edge states. Our model is based on a semiclassical approach where we define a local momentum distribution function, $f_\sigma(x, p)$, at each point x along a given edge. Here $\sigma = \pm$ is used to label the two layers, and p is the Landau gauge momentum used to label states within the lowest Landau level. The use of a semiclassical distribution function is justified since the experiments we are interested in are performed on macroscopic samples. We assume, as in the Landauer-Buttiker transport theory, that electrons exiting from a current lead have an equilibrium thermal distribution with a chemical potential equal to that of the lead. The evolution of the distribution function along a path between current leads is determined by the following relaxation-time-approximation Boltzmann equation:

$$\frac{\partial f_\sigma(x, p)}{\partial x} = \frac{1}{\xi} [f_\sigma(x, p) - f_{-\sigma}(x, p)] - \frac{1}{\eta} [f_\sigma(x, p) - f_\sigma^T(x, p)], \quad (1)$$

where

$$f_\sigma^T(x, p) = \{\exp[\epsilon(p) - \mu_\sigma(x)]\beta + 1\}^{-1}. \quad (2)$$

is the local equilibrium thermal distribution function. In the two terms on the right hand side of Eq. (1) the phenomenological parameters ξ and η are relaxation lengths for inter-edge and intra-edge equilibration. This equation describes the evolution of the distribution function along one edge of the sample; there is no equilibration between opposite edges on a Hall plateau. The form of this equation reflects the constant velocity of edge electrons at the Fermi level which allows the temporal relaxation to fix the position dependence of the distribution functions.

At each position the distribution function is partially characterized by a position dependent effective chemical potential $\mu_\sigma(x)$, defined by the following equation:

$$\int_{p_0}^{p_1} dp [f_\sigma(x, p) - f_\sigma^T(x, p)] = 0. \quad (3)$$

Here p_0 and p_1 are cutoff momenta, which satisfy $f_\sigma(x, p_1) \ll 1$ and $1 - f_\sigma(x, p_0) \ll 1$, so that $\mu_\sigma(x)$ is independent of the choice of both p_0 and p_1 . We will see that the only quantity needed for our semiclassical transport theory is $\mu_\sigma(x)$. In the edge region we may linearize the energy spectrum letting $\epsilon(p) = v_F p$, where v_F is the velocity of electrons in edge states. With this linearization the Boltzmann equation can be rewritten as a differential equation for $\mu_\sigma(x)$:

$$\frac{d\mu_\sigma(x)}{dx} = -\frac{1}{\xi} [\mu_\sigma(x) - \mu_{-\sigma}(x)]. \quad (4)$$

This equation [10] is easily solved;

$$\mu_\sigma(x) = \frac{1}{2}(1 + e^{-2x/\xi})\mu_\sigma(0) + \frac{1}{2}(1 - e^{-2x/\xi})\mu_{-\sigma}(0). \quad (5)$$

The current along an edge in layer σ is given at position x by

$$I_\sigma(x) = \frac{e}{h} \int_{p_0}^{p_1} \frac{d\epsilon(p)}{dp} f_\sigma(x, p). \quad (6)$$

In this expression for the current it is important to choose the interior cutoff p_0 such that $\epsilon(p_0)$ has the same value on right-going and left-going edges of the two layers. The lower cutoff momentum provides a practical definition of the edge regions. (With this definition, the net contribution to the current from the bulk region is zero.) Using the linearization of the energy spectrum the current carried at position x along an edge in layer σ may also be expressed in terms of $\mu_\sigma(x)$:

$$I_\sigma(x) = \frac{e}{h} [\mu_\sigma(x) - \epsilon(p_0)]. \quad (7)$$

The contact configurations we wish to model generally include ones in which voltage probes independently contact a single layer at some point along one of its edges.

Assuming ideal contacts in the Landauer-Buttiker transport theory sense, voltage probes measure the local chemical potential $\mu_\sigma(x)$ and although they alter the distribution function they do not alter the local effective chemical potential. Hence they play a completely passive role in our theory. Current probes, on the other hand, fix the difference between the incoming current and outgoing current as well as resetting the chemical potential of the outgoing electrons. We apply this theoretical framework first to examine the effect on transport in the quantum Hall regime of coupling to a floating layer. We apply Eq. (5) separately to the left-going and right-going edges as indicated in Fig. 1. For the right-going edge, the effective chemical potential on the left side of the contacted ($\sigma = -$) layer is fixed at the chemical potential of the source (μ_S) while the chemical potential on the left side of the floating layer ($\mu_+(0)$) is not immediately known. The right-going states of the two layers move toward equilibrium moving from left to right along the edge in accord with Eq. (5), reaching $\mu_-(L)$ and $\mu_+(L)$ as the drain contact is approached. Similarly along the left-going edge the chemical potential of the contacted layer at the right-side of the sample is fixed by the chemical potential of the drain (μ_D) and the chemical potential of the floating layer is $\mu_+(L)$. The equilibration of the two-layers along the left going edge is again described by Eq. (5). Setting the value of the effective chemical potential at the left side of the floating layer to $\mu_+(0)$ gives a self-consistent equation which allows the relative values of all effective chemical potentials to be related to the net current flowing through the sample. We find that

$$\mu_S - \mu_D = \frac{hI}{e} \left[\frac{1}{1 + \exp(-2L/\xi)} + \frac{1}{2} \right], \quad (8)$$

$$\mu_+(0) = \frac{hI}{2e} + \mu_D, \quad (9)$$

where L is the distance along the edges between source and drain. Because the equilibration between contacted and floating layers occurs gradually along the layer, the measured longitudinal ($R_{xx} = R_{12} = R_{34}$) and Hall ($R_{xy} = R_{13}$) resistances are dependent on the placement of the voltage probes:

$$R_{xx} = \frac{h}{e^2} \frac{\exp(-2a/\xi)[1 - \exp(-2b/\xi)]}{2[1 + \exp(-2L/\xi)]}, \quad (10)$$

$$R_{xy} = \frac{h}{e^2} \frac{1 + \exp(-2a/\xi) + \exp[-2(L-a)/\xi] + \exp(-2L/\xi)}{2[1 + \exp(-2L/\xi)]}. \quad (11)$$

where a and b specify the voltage probe positions as indicated in Fig. 1.

Note that in the limit of weak inter-layer coupling ($\xi \rightarrow \infty$), R_{xx} which would be zero for decoupled layers has a correction at first order in ξ^{-1} : $R_{xx} \simeq (h/e^2)(b/2\xi)$.

In a Landauer-Buttiker picture dissipation is associated with back-scattering between left-going states on one sample edge and right-going states on the opposite sample edge. In this system backscattering in the contacted layer occurs indirectly by tunneling to the floating layer and drifting around its perimeter to the other side of the sample before tunneling back to the contacted layer. The weak-coupling correction to the quantized Hall resistivity value, (h/e^2) , is second order in ξ^{-1} and vanishes as the voltage probes go toward the end of the Hall bar: $R_{xy} \simeq (h/e^2)[1 - a(L - a)/\xi^2]$. Thus R_{xy} can be nearly quantized even when R_{xx} is a substantial fraction of h/e^2 . In the opposite limit of strong inter-layer coupling ($\xi \rightarrow 0$), R_{xx} vanishes, and R_{xy} takes a quantized value of $h/2e^2$. In this strong coupling limit we get the same results as we would for a system where both layers are contacted. The overall behavior of resistances are shown in Fig. 2 for the choice of $a/L = 0.2$ and $b/L = 0.6$. The non-locality of the resistances, which depend on a , b , and L should be noted. In general the peak of R_{xx} occurs around $L \simeq \xi$ for a symmetrical system where $L = 2a + b$. The approximate value of the peak is $(b/3L)(h/e^2)$, except when b is quite close to L in which case it increases more rapidly and reaches the limiting value $h/2e^2$ at $b = L$.

The present theoretical scheme can be applied to various other lead geometries, including ones where leads are also attached to the floating layer. If only voltage probes are attached to this layer, it is possible to measure the “transresistances”, R_{xx}^t and R_{xy}^t , the ratios of voltages measured in the open layer to the net current [4-6]. Our scheme gives $R_{xx}^t = -R_{xx}$, and $R_{xy}^t = h/e^2 - R_{xy}$ in this case. Current leads can also be attached to the both layers. Experimentally it is easy to let either the source or the drain make contact to both layers. The resistivities measured in the lower layer for the case where the source is connected to both layers and the drain is connected only to the lower layer is $R_{12} = 0$, $R_{13} = (h/2e^2)\{1 + \exp[-2(a+b)/\xi]\}$, and $R_{34} = (h/2e^2)\exp(-2a/\xi)[1 - \exp(-2b/\xi)]$. Thus in this case the correction to the quantized Hall resistance is also linear in ξ^{-1} [13]. Another geometry of interest is realized when the voltage probes in the top layer are used as current leads. When the two current leads to the top layer are connected by an ideal conductor, current through the leads, I_+ , is induced by the current in the minus layer, I_- . For simple situations where a in Fig. 1 is 0 or $L/2$, the current through the leads 1 and 4 is given by $I_{+,14}/I_- = [1 - \exp(-2L/\xi)]/[3 + \exp(-2L/\xi)]$, and $I_{+,14}/I_- = [1 - \exp(-L/\xi)]^2/[3 + \exp(-2L/\xi)]$, respectively, where I_- is the current through the source and drain in the minus layer, as usual. In both cases, the ratio of the currents can be as large as 1/3 in the strong coupling regime. We remark that the transresistances and induced currents discussed here originate purely from tunneling between the two layers. Similar effects can also be provided by the frictional drag by the Coulomb interaction [4,11] although the drag resistances

tend to be much smaller.

We now compare these results with the experiments by Ohno and Sakaki [3,12]. Their results, Fig. 3 in ref. [3] clearly show that the experimental situation is in the weak inter-layer tunneling regime. At first sight this is surprising since the hopping amplitude in the bulk of their samples, responsible for the splitting between symmetric and antisymmetric subbands, was estimated to be $\Delta_{\text{SAS}} \simeq 0.02\text{meV}$. If the edges of their two samples were perfectly aligned we would estimate that $\xi = \hbar v_F / \Delta_{\text{SAS}}$ where $v_F \sim \ell \omega_c$ is the velocity of edge states in the abrupt edge limit. (ℓ is the magnetic length and ω_c is the cyclotron frequency.) Since $L = 200\mu\text{m}$, this estimate gives $L/\xi \sim 50$, well into the strong coupling regime. A likely cause of this discrepancy is disorder at the edge which results in random misalignment of the edge states in the two layers. Such a situation can be caused by roughness at the mesa-etched sample wall. Since vertical tunneling is possible only where the edges are aligned, disorder will drastically increase the tunneling length [14]. Support for this picture is found in the observed [12] weak dependence of coupling on the orientation of the magnetic field with respect to the normal to the two-dimensional layers. Even when the magnetic field is tilted in the direction perpendicular to the current direction, the values of the resistance shows little change. If the edges were perfectly aligned, in-plane magnetic field would reduce the hopping amplitude, and reduce the minimum value of R_{xx} noticeably. However, such a reduction does not occur when the hopping amplitude has already been reduced by the misalignment [14].

A remarkable result of the experiment is that there are peaks in R_{xx} on the high field side of the QH plateaus [3]. These peaks occur between the R_{xx} minimum and the ordinary peaks of R_{xx} which exist between the plateaus. This peak in the higher field side of the plateau can be understood as a phenomenon caused by the increase of the hopping amplitude as the magnetic field is increased: On the high field side, the Fermi edges continuously move towards the center of the sample. This causes three effects: (i) v_F is reduced, (ii) the size of the edge region increases, and (iii) the alignment of the two edges improves. All of these effects make L/ξ larger. Figure 2 tells us that if the hopping amplitude is continuously increased from near the origin, R_{xy} decreases from h/e^2 towards $h/2e^2$, and R_{xx} shows a peak. It should be noted that in our model the height of the peak depends only on the geometry of the sample, and on the ratios a/L and b/L . Our estimates for the height, about $5\text{k}\Omega$ ($2.5\text{k}\Omega$) for Landau level filling factor 1 (2), are consistent with the experiment [3,12,15]. Our theory suggests that this additional peak in R_{xx} and the nearly quantized Hall plateau occur in systems studied in these experiments because their bulk states are strongly coupled but their edge states are close to the weak coupling limit. The experimental results also show peaks on the low field side of the R_{xx} minimum. This peak is not separated from the ordinary peak of R_{xx} . This peak originates from the bottom of

the higher Landau level, so that conduction in the bulk is important and our theory cannot be applied.

In summary we have developed a theory which relates the transport properties of double-layer 2DES's near quantum Hall plateaus to inter-layer equilibration lengths along the sample edges. Our results permit a consistent interpretation of recent floating-layer experiments and can be applied to other contacting geometries. We anticipate that our theory will be useful in interpreting experiments whose aim is to probe the disorder and interaction physics of quantum Hall effect edge states.

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FIG. 1. Geometry of the sample. Two identical layers are stacked vertically. The leads (source, drain, 1, 2, 3, and 4) can contact both layers or either layer. The drift directions along the edges are indicated by arrows. The lengths L , a , and b specify the length of the sample and the positions of the leads.

FIG. 2. Longitudinal and Hall Resistances as a function of L/ξ . Here ξ is the inter edge relaxation length.

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